

ICEMOS Technology SOI Solutions



Introduction

ICEMOS uses the 10+ years of experience in SOI manufacturing at their Belfast site (previously BCO Technologies) to offer the marketplace world class custom SOI solutions.

Our highly skilled team has many years of SOI design and manufacturing experience to help develop an SOI solution to your requirement. We can support customers from small volume R&D quantities to large volume production quantities in excess of '000s wafers per month.

Our world class product quality, competitive cost structure plus rapid turnaround makes ICEMOS Technology your ideal SOI partner

Applications

Our customised SOI solutions are used in the following fields:

- SOI solutions for MEMS/MST
- Bio MEMS
- RF MEMS
- Optoelectronics
- Smart Power
- Advanced Analog ICs

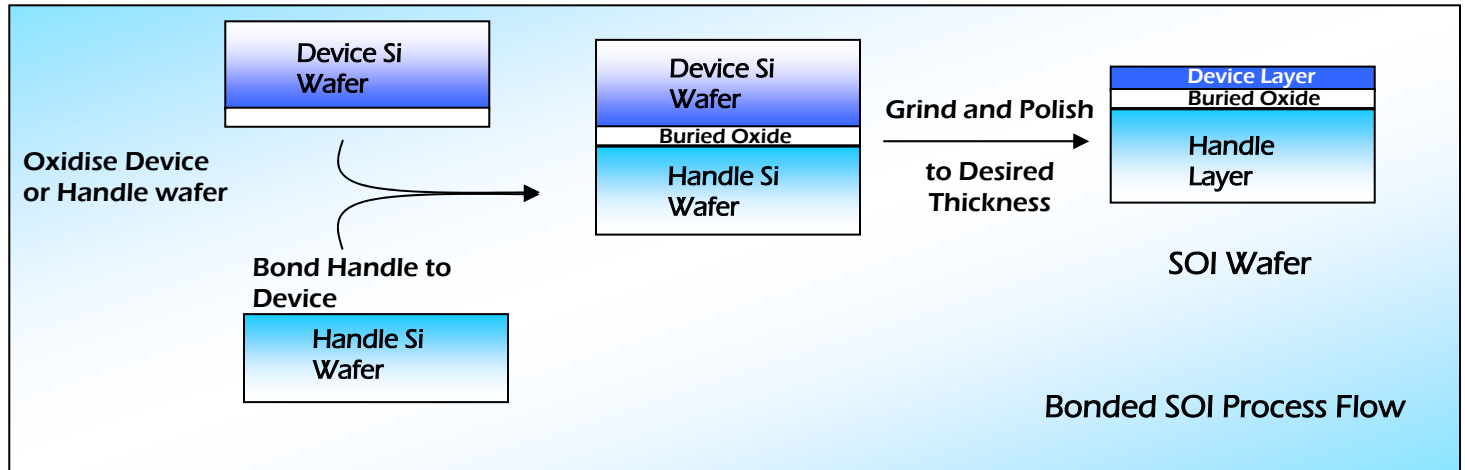
End Markets

- Telecommunications
- Medical
- Automotive
- Consumer
- Instrumentation

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SOI Specifications

Parameter	Unit	Specification Range
Wafer Diameter	Mm	100, 125, 150
Handle Layer Specifications		
Handle Thickness	μm	350 – 700
Handle Thickness Tolerance	μm	+/- 5
Dopant Type		N or P
Doping		N-Type: Sb, As, P; P-Type: B
Resistivity	$\Omega\text{-cm}$	>0.007
Growth Method		CZ or FZ
Crystal Orientation		<100> or <111>
Backside Finish		Lapped/Etched or Polished
Buried Oxide Specifications		
Thermally Oxidised Buried Oxide Thickness	μm	0.2 – 4.0 grown on Handle, Device or both wafers
Device Layer Specifications		
Device Layer Thickness	μm	2 – 200
Tolerance	μm	+/- 0.5 or +/- 1
Dopant Type		N or P
Doping		N-Type: Sb, As, P; P-Type: B
Resistivity	$\Omega\text{-cm}$	>0.007
Growth Method		CZ or FZ
Crystal Orientation		<100> or <111>
Buried Layer Implant		N- Type of P-Type